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- (71) Applicant (*for all designated States except US*): LEIV EIRIKSSON NYSKAPING AS [NO/NO]; Postboks 1262, Pirsenteret, N-7462 Trondheim (NO).
- (72) Inventors; and
- (75) Inventors/Applicants (*for US only*): BUGGE, Renato [NO/NO]; Haugnessvingen 20A, N-7462 Trondheim (NO). FIMLAND, Bjørn-Ove [NO/NO]; Marie Sjørdalsvei 14G, N-7036 Trondheim (NO).
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(54) Title: ETCHING OF ALGAINASSB

(57) Abstract: The present invention relates to a wet acid etchant for wet acid etching of intrinsic, n-doped or p-doped $Al_{1-x}zGa_xIn_zAs_{1-y}Sb_y$ with $0 < x < 1$, $0 < y < 1$, $0 \leq z < 1$ and $0 < x+z < 1$, a process for wet acid etching of intrinsic, n-doped or p-doped $Al_{1-x}zGa_xIn_zAs_{1-y}Sb_y$ with $0 < x < 1$, $0 < y < 1$, $0 \leq z < 1$ and $0 < x+z < 1$, and a semiconductor structure prepared by wet acid etching of $Al_{1-x}zGa_xIn_zAs_{1-y}Sb_y$ with $0 < x < 1$, $0 < y < 1$, $0 \leq z < 1$ and $0 < x+z < 1$. The etchant comprises: organic acid; oxidizing agent; hydrofluoric acid.

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